

L Number	Hits	Search Text	DB	Time stamp
1	79	selectiv\$4 near3 etch\$4 near4 (epitax\$4) same nitride	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 09:19
2	44	(gehrke.in. or linthicum.in.) and gallium adj nitride	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 09:19
-	2	layer\$3 same substrate same (gan or gallium adj nitride or sapphire or zinc adj oxide or zno or silicon adj carbide or silicon or si or sic) and two near2 sid\$3 same deposit\$4) and 117/84-109.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/23 16:01
-	15	two near1 layer\$3 near3 substrate near4 (gan or gallium adj nitride or sapphire or zinc adj oxide or zno or silicon adj carbide or silicon or si or sic) and 117/\$4.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/23 16:11
-	38	multi\$1layer\$3 near3 substrate and 117/\$4.ccls. and (remov\$3 near2 substrate)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/23 16:21
-	2	two near1 sid\$3 near4 deposit\$4 and 117/\$4.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/23 16:43
-	96	double near2 sid\$2 near2 (epitax\$4 or deposit\$4)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/23 16:27
-	16	heat\$4 near10 lamp same cvd same (reactor or chamber) same inside and epitax\$4	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/02 16:07
-	13	heat\$4 near10 lamp near11 (insid\$4 or intern\$4) same cvd	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/02 16:11
-	23	heat\$4 near10 lamp same cvd same (reactor or chamber) same direct\$4 and epitax\$4	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:37
-	4	layered near5 substrate same bow\$4	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:42
-	33	layered near5 substrate same sapphire same nitride	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 10:10
-	54	(multi\$1layer\$1) near2 substrate same sapphire	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 10:21

	6	(multi\$1layer\$1) near2 substrate same (warp\$4 or bow\$4) same nitride	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 10:14
	3	(multi\$1layer\$1) near2 substrate same (warp\$4 or bow\$4) and epitax\$4	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 10:14
	38	rotat\$4 near4 substrate near4 stationar\$4 same uniform\$4	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 10:54
	34	rotat\$4 near4 substrate near4 stationar\$4 and (CVD)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 11:49
	29	remov\$4 near3 substrate same epitax\$4 same polish\$4 same nitride	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 11:49
	9	remov\$4 near3 substrate same polish\$4 and 117/915.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 11:54
	30	electrochemical near3 polish\$4 same mechanical near3 polish\$4 same substrate	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 13:24
	18	layered near3 substrate and "iii-v" and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 13:45
	21	layered near2 substrate same warp\$3	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 13:41
	78	layered near3 substrate and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 14:19
	25	(Gan or gallium adj nitride) near4 thick near6 epitax\$4 same sapphire near2 substrate	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 15:23
	33	pattern\$4 near4 (GaN or gallium near2 nitride) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 16:19
	99	pattern\$4 near4 (GaN or gallium near2 nitride) and 257/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 16:21
	31	selectiv\$4 near3 etch\$4 near4 (GaN or gallium near2 nitride) and 257/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/03 16:24

-	10	selectiv\$4 near3 etch\$4 near4 (epitax\$4 near5 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IEM TDB	2003/06/03 16:26
-	11	selectiv\$4 near3 etch\$4 near4 (epitax\$4 same "ili-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IEM TDB	2003/06/04 09:16